In the Claims

The following Listing of Claims replaces all prior versions in the application:

LISTING OF CLAIMS

1. (Currently Amended) A method for manufacturing at least one electrode on a II-VI semiconducting material or a compound of ~~this material~~ the II-VI semiconductor material, ~~this electrode~~ the at least one electrode being in a metal for which the work function is substantially equal to or larger than that of ~~the II-VI semiconductor~~ the II-VI semiconducting material, this method being characterized in that the ~~electrode~~ the at least one electrode is formed by electrochemical deposition of the metal from a solution of a chloride of the metal in a hydrochloric acid solution, wherein the hydrochloric acid solution consists essentially of pure hydrochloric acid diluted by less than about 80% water by weight.

2. (Currently Amended) The method according to claim 1, wherein the metal is gold or platinum and ~~a gold or platinum chloride solution in pure hydrochloric acid~~ a gold chloride solution or a platinum chloride solution in pure hydrochloric acid is used.

3. (Currently Amended) The method according to claim 2, wherein ~~the concentration of gold or platinum chloride~~ a concentration of gold chloride or platinum chloride in pure hydrochloric acid is less than 5%.

4. (Currently Amended) The method according to claim 1, wherein ~~the surface of the material~~ a surface of the material is prepared before the deposition in order to make this surface capable of fixing the metal.

5. (Original) The method according to claim 4, wherein the surface of the material is chemically etched.

6. (Currently Amended) The method according to claim 5, wherein the metal is gold or platinum, a gold or platinum chloride solution in pure hydrochloric acid is used and a solution of bromine and ~~preferably pure hydrochloric acid~~ hydrochloric acid is used for the chemical etching.

7. (Currently Amended) The method according to claim 1, wherein ~~the material~~ the II-VI semiconducting material is CdTe.

8. (Currently Amended) The method according to claim 7, wherein ~~the electrode~~ the at least one electrode is formed on ~~a material~~ a compound of CdTe which is selected from CdZnTe, CdTe:Cl, CdTeSe:Cl, CdZnTe:Cl, CdTe:In, CdZnTe:In and CdHgTe.

9. (New) The method according to claim 6, wherein a solution of bromine and pure hydrochloric acid is used for the chemical etching.

10. (New) The method according to claim 1, wherein the hydrochloric acid solution consists essentially of pure hydrochloric acid.